2N5401

Preferred Device

Amplifier Transistors

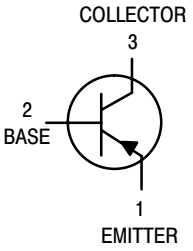
PNP Silicon

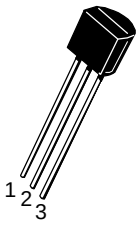
Features

- Pb−Free Packages are Available*

ON Semiconductor®

http://onsemi.com





TO−92
CASE 29
STYLE 1

MAXIMUM RATINGS

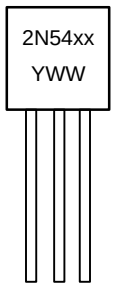
Rating	Symbol	2N5400	2N5401	Unit
Collector − Emitter Voltage	V_{CEO}	120	150	Vdc
Collector − Base Voltage	V_{CBO}	130	160	Vdc
Emitter − Base Voltage	V_{EBO}	5.0		Vdc
Collector Current − Continuous	I_C	600		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction−to−Case	$R_{\theta JC}$	83.3	°C/W

MARKING DIAGRAM



Y = Year
WW = Work Week

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

Preferred devices are recommended choices for future use and best overall value.